

查询ZVN4206A供应商

捷多邦，专业PCB打样工厂

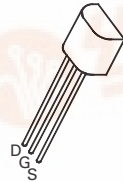
, 24小时加急出货

N-CHANNEL ENHANCEMENT MODE VERTICAL DMOS FET

ISSUE 2 – JUNE 94

FEATURES

- * 60 Volt V_{DS}
- * $R_{DS(on)} = 1 \Omega$



E-LINE
TO92 COMPATIBLE

ABSOLUTE MAXIMUM RATINGS.

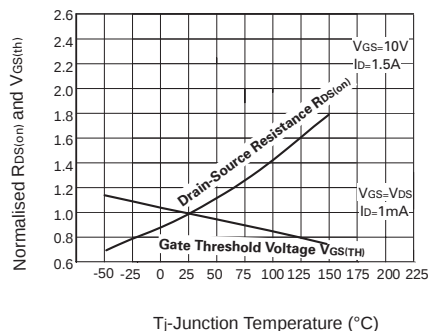
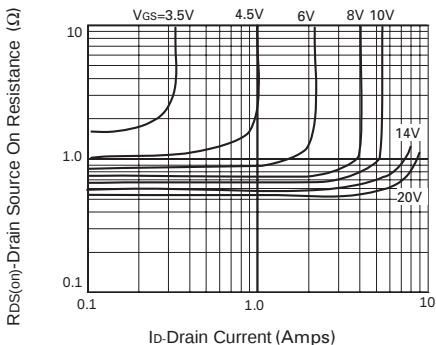
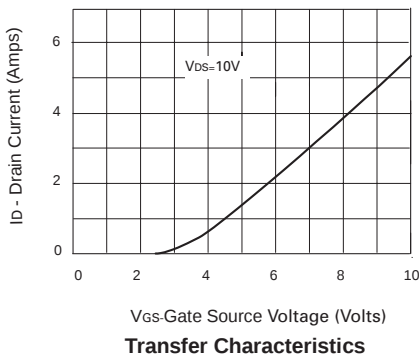
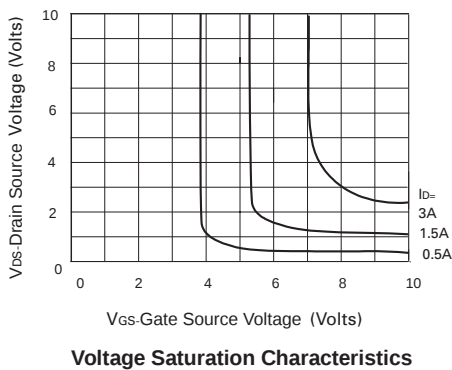
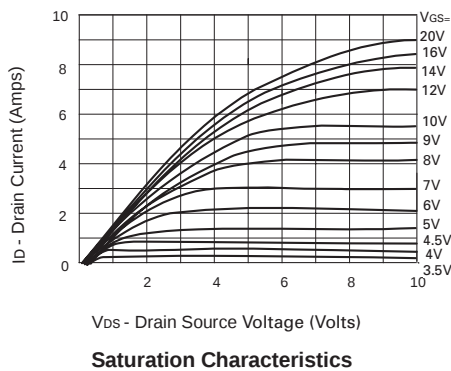
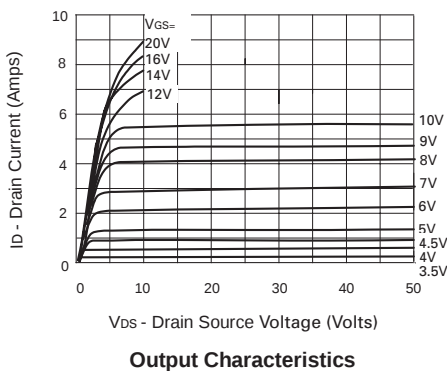
PARAMETER	SYMBOL	VALUE	UNIT
Drain-Source Voltage	V_{DS}	60	V
Continuous Drain Current at $T_{amb}=25^{\circ}\text{C}$	I_D	600	mA
Pulsed Drain Current	I_{DM}	8	A
Gate-Source Voltage	V_{GS}	± 20	V
Power Dissipation at $T_{amb}=25^{\circ}\text{C}$	P_{tot}	0.7	W
Operating and Storage Temperature Range	$T_j:T_{stg}$	-55 to +150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Drain-Source Breakdown Voltage	BV_{DSS}	60		V	$I_D=1\text{mA}$, $V_{GS}=0\text{V}$
Gate-Source Threshold Voltage	$V_{GS(th)}$	1.3	3	V	$I_D=1\text{mA}$, $V_{DS}=V_{GS}$
Gate-Body Leakage	I_{GSS}		100	nA	$V_{GS}=\pm 20\text{V}$, $V_{DS}=0\text{V}$
Zero Gate Voltage Drain Current	I_{DSS}		10 100	μA μA	$V_{DS}=60\text{V}$, $V_{GS}=0$ $V_{DS}=48\text{V}$, $V_{GS}=0\text{V}$, $T=125^{\circ}\text{C}$ (2)
On-State Drain Current(1)	$I_{D(on)}$	3		A	$V_{DS}=25\text{V}$, $V_{GS}=10\text{V}$
Static Drain-Source On-State Resistance (1)	$R_{DS(on)}$		1 1.5	Ω Ω	$V_{GS}=10\text{V}$, $I_D=1.5\text{A}$ $V_{GS}=5\text{V}$, $I_D=500\text{mA}$
Forward Transconductance(1)(2)	g_{fs}	300		mS	$V_{DS}=25\text{V}$, $I_D=1.5\text{A}$
Input Capacitance (2)	C_{iss}		100	pF	$V_{DS}=25\text{V}$, $V_{GS}=0\text{V}$, $f=1\text{MHz}$
Common Source Output Capacitance (2)	C_{oss}		60	pF	
Reverse Transfer Capacitance (2)	C_{rss}		20	pF	
Turn-On Delay Time (2)(3)	$t_{d(on)}$		8	ns	$V_{DD} \approx 25\text{V}$, $I_D=1.5\text{A}$
Rise Time (2)(3)	t_r		12	ns	
Turn-Off Delay Time (2)(3)	$t_{d(off)}$		12	ns	
Fall Time (2)(3)	t_f		15	ns	

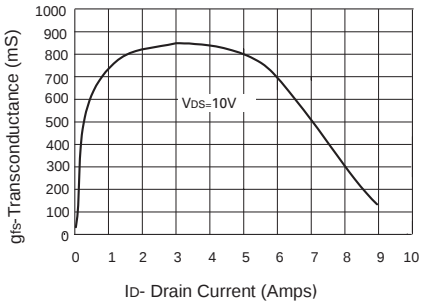
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TYPICAL CHARACTERISTICS

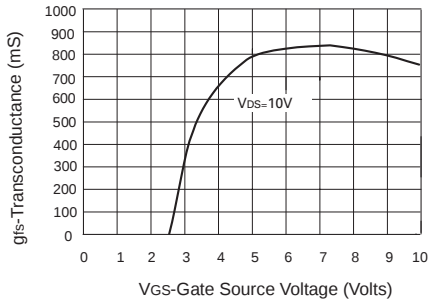


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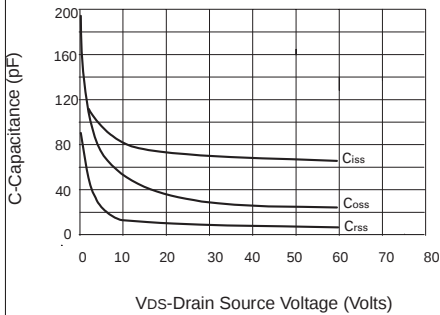
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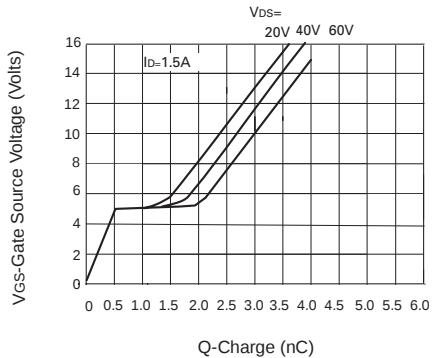
Transconductance v drain current



Transconductance v gate-source voltage



Capacitance v drain-source voltage



Gate charge v gate-source voltage